

IN THE CLAIMS

Claims 1-35 (canceled)

36. (New): A multiwall carbon nanotube arrangement, comprising a substrate and at least one multiwall carbon nanotube, wherein the at least one multiwall carbon nanotube comprises:

an outer wall, the outer wall being substantially oxidized wherein the substantial oxidation leads to an electrically insulating effect so that the outer wall of the multiwall carbon nanotube loses its ability to conduct electric current;

at least one inner wall, the at least one inner wall not being oxidized and wherein the conduction of electricity through the multiwall carbon nanotube is automatically taken over by the at least one inner wall after the substantial oxidation of the outer wall; and

wherein, due to the substantial oxidation of the outer wall, the at least one multiwall carbon nanotube is bound covalently to the substrate.

37. (New): A multiwall carbon nanotube arrangement as in claim 36, further comprising the nanotube being doped with boron nitride.

38. (New): A multiwall carbon nanotube arrangement as in claim 36, further comprising the substrate being an electronic component.

39. (New): A multiwall carbon nanotube arrangement as in claim 37, further comprising the substrate being an electronic component.

40. (New): A process for substantially oxidizing only the outer wall of a multiwall carbon nanotube and binding the multiwall carbon nanotube to a substrate, wherein the substantial oxidation of only the outer wall leads to an electrically insulating effect and wherein the outer wall of the multiwall carbon nanotube loses its ability to conduct electric current and wherein the conduction of electricity through the multiwall carbon nanotube is automatically taken over by the next inner nanotube and wherein, due to the substantial oxidation of the outer wall, the multiwall carbon nanotube is bound covalently to the substrate, the process comprising:

providing a multiwall carbon nanotube;

subjecting the multiwall carbon nanotube to substantial oxidation; and

bringing the multiwall carbon nanotube into contact with the substrate.

41. (New) the process of claim 40, further comprising carrying out the substantial oxidation by reaction with an acid selected from the group consisting of nitric acid, sulfuric acid, chromic acid, Caro's acid, perchloric acid, iodic acid, and an organic peracid.

42. (New): The process of claim 41, further comprising using sulfuric acid as a mixture with hydrogen peroxide.

43. (New): The process as claimed in any of claims 40 to 42, further comprising carrying out the substantial oxidation of the outer wall of the multiwall carbon nanotube at a temperature up to the boiling point of the respective reaction mixture.

44. (New): The process as claimed in any of claims 40 to 42, further comprising doping the multiwall carbon nanotube with boron nitride.

45. (New): The process as claimed in any of claims 40 to 42, further comprising ensuring the substrate is bearing chemically reactive groups or coating the substrate with a further material bearing chemically reactive groups.

46. (New): The process as claimed in claim 40, further comprising:
carrying out the substantial oxidation of the outer wall of the multiwall carbon nanotube at a temperature up to the boiling point of the respective reaction mixture; and
ensuring the substrate is bearing chemically reactive groups or coating the substrate with a further material bearing chemically reactive groups.

47. (New): The process as claimed in claim 40, further comprising:
ensuring the substrate is bearing chemically reactive groups or coating the substrate with a further material bearing chemically reactive groups; and
doping the multiwall carbon nanotube with boron nitride.

48. (New): The process as claimed in claim 40, further comprising:
carrying out the substantial oxidation of the outer wall of the multiwall carbon nanotube at a temperature up to the boiling point of the respective reaction mixture;
ensuring the substrate is bearing chemically reactive groups or coating the substrate with a further material bearing chemically reactive groups; and
doping the multiwall carbon nanotube with boron nitride.

49. (New): The process as claimed in any of claims 40 to 42, further comprising separating off the multiwall carbon nanotube prior to bringing it into contact with the substrate.

50. (New): The process of claim 40, further comprising:
ensuring the substrate is bearing chemically reactive groups or coating the substrate with a further material bearing chemically reactive groups; and
separating off the multiwall carbon nanotube prior to bringing it into contact with the substrate.

51. (New): The process of claim 40, further comprising:
carrying out the substantial oxidation of the outer wall of the multiwall carbon nanotube at a temperature up to the boiling point of the respective reaction mixture; and
separating off the multiwall carbon nanotube prior to bringing it into contact with the substrate.

52. (New): The process of claim 40, further comprising:
doping the multiwall carbon nanotube with boron nitride; and
separating off the multiwall carbon nanotube prior to bringing it into contact with the substrate.

53. (New): The process of claim 40, further comprising:
ensuring the substrate is bearing chemically reactive groups or coating the
substrate with a further material bearing chemically reactive groups;
carrying out the substantial oxidation of the outer wall of the multiwall carbon
nanotube at a temperature up to the boiling point of the respective reaction
mixture;
doping the multiwall carbon nanotube with boron nitride; and
separating off the multiwall carbon nanotube prior to bringing it into contact with
the substrate.